

TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

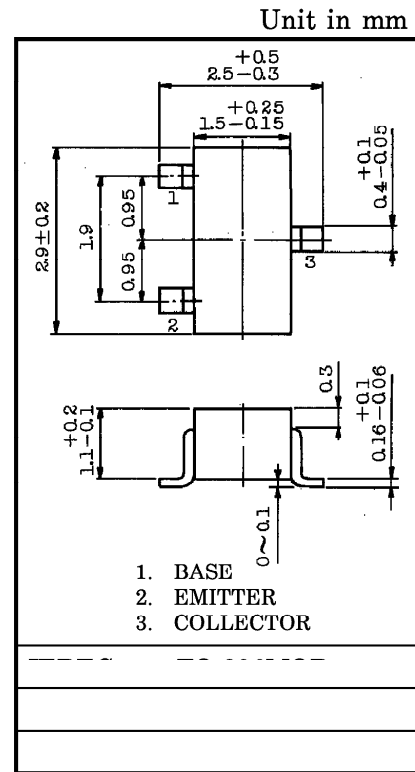
AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.

- High Voltage and High Current
: $V_{CEO}=50V$, $I_C=150mA$ (Max.)
- Excellent h_{FE} Linearity
: $h_{FE}(I_C=0.1mA)/h_{FE}(I_C=2mA)=0.95$ (Typ.)
- High h_{FE} : $h_{FE}=70\sim700$
- Low Noise : $NF=1dB$ (Typ.), $10dB$ (Max.)

- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	$-55\sim125$	$^\circ C$



Weight : 0.012g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V$, $I_E=0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V$, $I_C=0$	—	—	0.1	μA
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=6V$, $I_C=2mA$	70	—	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$, $I_B=10mA$	—	0.1	0.25	V
Transition Frequency	f_T	$V_{CE}=10V$, $I_C=1mA$	80	—	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$, $I_E=0$, $f=1MHz$	—	2.0	3.5	pF
Noise Figure	NF	$V_{CE}=6V$, $I_C=0.1mA$, $f=1kHz$, $R_g=10k\Omega$	—	1.0	10	dB

Note : h_{FE} Classification

O (O) : 70~140, Y (Y) : 120~240, GR (G) : 200~400,

BL (L) : 350~700

() Marking Symbol

MARKING

